TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7SL00F, TC7SL00FU

2-INPUT NAND GATE

The TC7SL00 is a low voltage operative C²MOS 2-INPUT NAND GATE fabricated with silicon gate C²MOS technology.

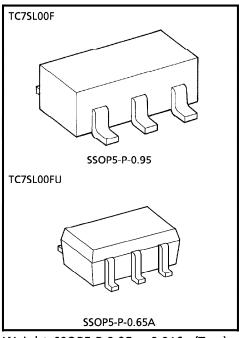
Operating voltage $(V_{CC(opr)})$ is 1~3V equivalent to 1pc or 2pcs of dry cell battery and it achives low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High Speed \cdots $t_{pd} = 10$ ns (Typ.) at $V_{CC} = 3V$
- Low Power Dissipation $\cdots I_{CC} = 1\mu A$ (Max.) at $Ta = 25^{\circ}C$
- High Noise Immunity $V_{NIH} = V_{NIL}$ = 28% V_{CC} (Min.)
- Symmetrical Output Impedance ····· |I_{OH}| = I_{OL} = 1mA
- Balanced Propagation Delay Time ··· tpLH≒tpHL
- Low Voltage Operating ·················V_{CC} (opr) = 1~3.6V

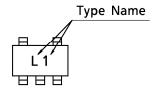


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~5	V
DC Input Voltage	VIN	-0.5~V _{CC} +0.5	V
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	V
Input Diode Current	ΙΚ	± 20	mA
Output Diode Current	lok	± 20	mA
DC Output Current	IOUT	± 12.5	mA
DC V _{CC} / Ground Current	lcc	± 25	mA
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10s)	TL	260	°C

MARKING



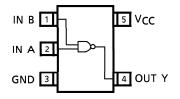
961001EBA2

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

LOGIC DIAGRAM

PIN CONNECTION (TOP VIEW)





RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	1~3.6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	VOUT	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
		$0\sim 1000 (V_{CC} = 1.0V)$	
Input Rise and Fall Time	t _r , t _f	$0\sim 500 (V_{CC} = 1.5V)$	ns
		0~ 400 (V _{CC} = 3.0V)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		TEST CIR-	TEST CONDITION			Ta = 25°C			Ta = − 40~85°C		UNIT
		CUIT			Vcc	MIN.	TYP.	МАХ.	MIN.	MAX.	OINIT
High Lovel Input					1.0	0.75	_	_	0.75	_	
High-Level Input \ Voltage	VIH	—		_	1.5	1.05	—	—	1.05	—	V
Voltage					3.0	2.10	_	_	2.10	_	
Low-Level Input			_		1.0	—	_	0.25	l —	0.25	
Voltage	V _{IL}	—			1.5	—	—	0.45	—	0.45	\ \ \
vortage					3.0	—	_	0.90	—	0.90	
				I _{OH} = -20μA	1.0	0.9	1.0	—	0.9	_	V
High-Level			V _{IN} = V _{IH} or V _{IL}		1.5	1.4	1.5	—	1.4	_	
Output Voltage	Voн	 			3.0	2.9	3.0	_	2.9	_	
				$I_{OH} = -1mA$	1.5	1.07	1.23	<u> </u>	0.99		
				$I_{OH} = -2.6mA$	3.0	2.61	2.68	—	2.55	_	
			V _{IN} = V _{IH}		1.0	_	0.0	0.1	—	0.1	
Low-Level Output Voltage				$I_{OL} = 20 \mu A$	1.5	—	0.0	0.1	—	0.1	
	VOL	—			3.0	_	0.0	0.1	—	0.1	V
				$I_{OL} = 1mA$	1.5	—	0.23	0.31	—	0.37	·]
				$I_{OL} = 2.6 mA$	3.0	_	0.23	0.31	<u> </u>	0.33	
Input Leakage	liki	_	V _{IN} = V _{CC}	or GND	3.6			± 0.1		± 1.0	
Current	IN		AIN - ACC	OI GIVD	3.0			- 0.1		∸ 1.0	ا ۸٫٫٫ ا
Quiescent Supply Current	l _{CC}	_	$V_{IN} = V_{CC}$	or GND	3.6	_	_	1.0	_	10.0	μΑ

961001EBA2'

The products described in this document are subject to foreign exchange and foreign trade control laws.
 The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
 The information contained herein is subject to change without notice.

CHARACTERISTIC SYMBO	CVMDOL	TEST	TEST CONDITION		UNIT		
	STIVIBOL	CUIT	1231 CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition	tTLH				5.0	9.0	ns
Time	tTHL	_	_	_	5.0	9.0	115
Propagation	^t PLH				7.5	13.0	nc
Delay Time	t _{PHL}		1	_	7.5	13.0	ns

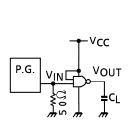
AC ELECTRICAL CHARACTERISTICS ($C_L = 25pF$, Input $t_r = t_f = 6ns$)

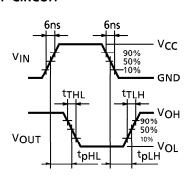
CHARACTERISTIC SYMBOL	CANADOL	TEST	TEST CONDITION 1		Ta = 25°C		Ta = -4			
	CIR- CUIT	1131 CONDITION	V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
Output Transition	4			1.0	_	70	170	_	240	
Output Transition Time	t _{TLH}	_	-	1.5	<u> </u>	25	45	<u> </u>	55	ns
Time	tTHL			3.0	<u> </u>	10	15		20	
Propagation	t n			1.0	_	70	170	_	210	
Propagation Delay Time	t _{PLH}	_	_	1.5	_	25	45	_	55	ns
Delay Time	t _{PHL}			3.0	_	10	15	_	20	
Input Capacitance	CIN	_	1		_	5	10		10	
Power Dissipation	Coo		Note (1)			10				рF
Capacitance	C _{PD}		Note (1)			10				

Note (1): CpD defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

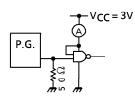
Average operating current can be obtained by the equation as follows. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

SWITCHING CHARACTERISTICS TEST CIRCUIT





ICC (opr) TEST CIRCUIT

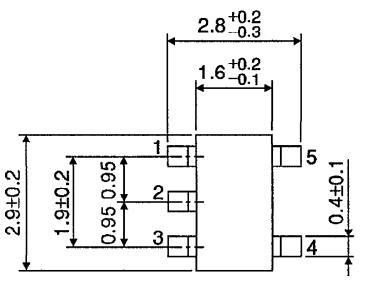


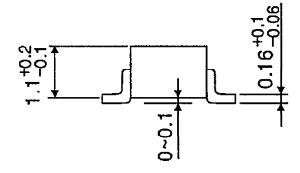
input waveform is the same as that in case of switching characteristics test.

Unit: mm

OUTLINE DRAWING

SSOP5-P-0.95

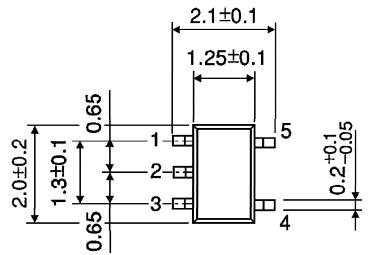




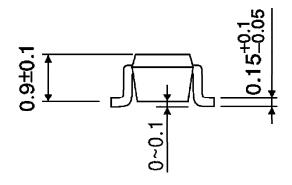
Weight: 0.016g (Typ.)

OUTLINE DRAWING

SSOP5-P-0.65A



Unit: mm



Weight: 0.006g (Typ.)